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ZnSe To Anthony find $b_{\text{eff}} = 0.015 \text{ eV}$ but $\chi^2 = 5.1 \text{ eV}^{-1} \text{ Jm}^{-2}$ is 4 lead theory and others.

conclusion: ϵ_{eff} conclusion to be untenable for all isovalent semicon-

and the "new" monolayer-like vertices have relative phase π .

The two-dimensional model of the system is shown in Fig. 1. The energy bands of the system are calculated by the standard tight-binding method.

Figure 2 shows the energy band structures of the system for the case of the Si_2S_3 monolayer. The energy bands of the system are calculated by the standard tight-binding method.

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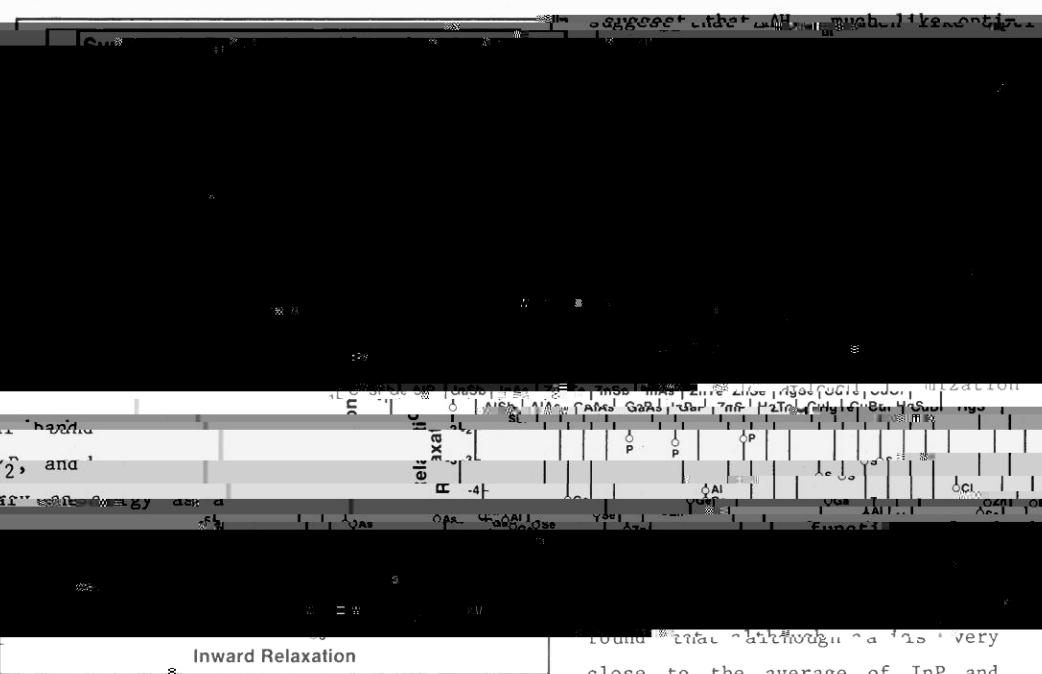


Fig. 1: Calculated¹² bond relaxation energy (eV) versus bond length (Å) for 'isovalent impurities' in semiconductors (abscissa). Asterisks denote experimental XAMS values.

found that although $r_{\text{In-P}}$ is very close to the average of InP and

lengths $r_{\text{Ga-P}}$ and $r_{\text{In-P}}$ are substantially different from

monatomic ($r_{\text{eq}} = 0.271$). Furthermore, the chalcocite arrangement was found to be substantially stabler than the zincblende arrangement: i.e. the total energy (E_T) minimization of $\text{In}_{0.5}\text{Ga}_{0.5}\text{S}_3$ (chalcocite) is negative, while that of